## Jiang Pu

## List of Publications by Citations

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16 2,594 41 33 g-index h-index citations papers 11.6 2,968 41 5.04 L-index avg, IF ext. citations ext. papers

#	Paper	IF	Citations
33	Large-area synthesis of highly crystalline WSe(2) monolayers and device applications. <i>ACS Nano</i> , <b>2014</b> , 8, 923-30	16.7	732
32	Highly flexible MoS2 thin-film transistors with ion gel dielectrics. <i>Nano Letters</i> , <b>2012</b> , 12, 4013-7	11.5	663
31	Monolayer MoSe2 grown by chemical vapor deposition for fast photodetection. <i>ACS Nano</i> , <b>2014</b> , 8, 858	32 <u>1</u> 807	413
30	Highly Flexible and High-Performance Complementary Inverters of Large-Area Transition Metal Dichalcogenide Monolayers. <i>Advanced Materials</i> , <b>2016</b> , 28, 4111-9	24	90
29	Fabrication of stretchable MoS2 thin-film transistors using elastic ion-gel gate dielectrics. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 023505	3.4	75
28	Ambipolar organic single-crystal transistors based on ion gels. <i>Advanced Materials</i> , <b>2012</b> , 24, 4392-7	24	75
27	2D Materials for Large-Area Flexible Thermoelectric Devices. <i>Advanced Energy Materials</i> , <b>2020</b> , 10, 1907	2 <b>842</b> 8	72
26	Charge transport in ion-gated mono-, bi-, and trilayer MoS2 field effect transistors. <i>Scientific Reports</i> , <b>2014</b> , 4, 7293	4.9	52
25	Flexible and stretchable thin-film transistors based on molybdenum disulphide. <i>Physical Chemistry Chemical Physics</i> , <b>2014</b> , 16, 14996-5006	3.6	50
24	Synthesis of Large-Area InSe Monolayers by Chemical Vapor Deposition. <i>Small</i> , <b>2018</b> , 14, e1802351	11	48
23	Monolayer Transition Metal Dichalcogenides as Light Sources. <i>Advanced Materials</i> , <b>2018</b> , 30, e1707627	24	46
22	Enhanced thermoelectric power in two-dimensional transition metal dichalcogenide monolayers. <i>Physical Review B</i> , <b>2016</b> , 94,	3.3	45
21	Thermoelectric Detection of Multi-Subband Density of States in Semiconducting and Metallic Single-Walled Carbon Nanotubes. <i>Small</i> , <b>2016</b> , 12, 3388-92	11	40
20	Self-Aligned and Scalable Growth of Monolayer WSe2MoS2 Lateral Heterojunctions. <i>Advanced Functional Materials</i> , <b>2018</b> , 28, 1706860	15.6	36
19	Electron-hole doping asymmetry of Fermi surface reconstructed in a simple Mott insulator. <i>Nature Communications</i> , <b>2016</b> , 7, 12356	17.4	32
18	A Versatile and Simple Approach to Generate Light Emission in Semiconductors Mediated by Electric Double Layers. <i>Advanced Materials</i> , <b>2017</b> , 29, 1606918	24	31
17	Recent Progress on Light-Emitting Electrochemical Cells with Nonpolymeric Materials. <i>Advanced Functional Materials</i> , <b>2020</b> , 30, 1908641	15.6	14

## LIST OF PUBLICATIONS

16	Two-dimensional ground-state mapping of a Mott-Hubbard system in a flexible field-effect device. <i>Science Advances</i> , <b>2019</b> , 5, eaav7282	14.3	13
15	Photodetection in pl junctions formed by electrolyte-gated transistors of two-dimensional crystals. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 201107	3.4	12
14	Simultaneous enhancement of conductivity and Seebeck coefficient in an organic Mott transistor. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 233301	3.4	9
13	Wafer-Scale Growth of One-Dimensional Transition-Metal Telluride Nanowires. <i>Nano Letters</i> , <b>2021</b> , 21, 243-249	11.5	8
12	Effects of electrolyte gating on photoluminescence spectra of large-area WSe2monolayer films. Japanese Journal of Applied Physics, <b>2016</b> , 55, 06GB02	1.4	6
11	Non-Fermi-liquid behavior and doping asymmetry in an organic Mott insulator interface. <i>Physical Review B</i> , <b>2019</b> , 100,	3.3	5
10	Air-stable and efficient electron doping of monolayer MoS by salt-crown ether treatment. <i>Nanoscale</i> , <b>2021</b> , 13, 8784-8789	7.7	4
9	Room-Temperature Chiral Light-Emitting Diode Based on Strained Monolayer Semiconductors. <i>Advanced Materials</i> , <b>2021</b> , 33, e2100601	24	4
8	Exciton Polarization and Renormalization Effect for Optical Modulation in Monolayer Semiconductors. <i>ACS Nano</i> , <b>2019</b> , 13, 9218-9226	16.7	3
7	CVD growth of large-area InS atomic layers and device applications. <i>Nanoscale</i> , <b>2020</b> , 12, 9366-9374	7.7	3
6	Nanowire-to-Nanoribbon Conversion in Transition-Metal Chalcogenides: Implications for One-Dimensional Electronics and Optoelectronics. <i>ACS Applied Nano Materials</i> , <b>2022</b> , 5, 1775-1782	5.6	2
5	Electrolyte-Gating-Induced Metal-Like Conduction in Nonstoichiometric Organic Crystalline Semiconductors under Simultaneous Bandwidth Control. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2019</b> , 13, 1900162	2.5	1
4	Semiconductors: Ambipolar Organic Single-Crystal Transistors Based on Ion Gels (Adv. Mater. 32/2012). <i>Advanced Materials</i> , <b>2012</b> , 24, 4463-4463	24	1
3	Electric Double Layer Doping of Charge-Ordered Insulators (BEDT-TTF)213 and (BETS)213. <i>Crystals</i> , <b>2021</b> , 11, 791	2.3	O
2	Nonpolymeric LECs: Recent Progress on Light-Emitting Electrochemical Cells with Nonpolymeric Materials (Adv. Funct. Mater. 33/2020). <i>Advanced Functional Materials</i> , <b>2020</b> , 30, 2070223	15.6	
1	Room-Temperature Chiral Light-Emitting Diode Based on Strained Monolayer Semiconductors (Adv. Mater. 36/2021). <i>Advanced Materials</i> , <b>2021</b> , 33, 2170282	24	